

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1448A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet

1

of

1

Complete if Known

Application Number	10/717,963
Filing Date	11/21/2003
First Named Inventor	SUMIO ASHIDA
Art Unit	2855 1256
Examiner Name	Unknown <i>Angel</i>
Attorney Docket Number	008312-0306969

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cltg No.	Foreign Patent Document Country Code* ³ Number* ⁴ Kind Code* ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
<i>W</i>		JP 2003-233931	08/2003	Kojima et al.		

**Examiner
Signature**

Date Considered

4/21/06

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.¹ Applicant's unique citation designation number (optional).² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document, by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

FORM PTO-1449 (modified)
To: U.S. Department of Commerce
(PW FORM PAT-1449)
Patent and Trademark Office



Atty. Dkt. No.	M#	Client Ref.
	008312-0306969	T7KO-03S1080

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

Applicant: ASHIDA et al.	
Appln. No.: 10/717,963	
Filing Date: November 21, 2003	
Examiner: <i>Unassigned</i> <i>[Signature]</i>	Group Art Unit: 2655 1756

Date: April 29, 2005

P ag e	1	of	1
--------------	---	----	---

U.S. PATENT DOCUMENTS

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
	AR					
	BR					
	CR					
	DR					
	ER					
	FR					
	GR					
	HR					
	IR					
	JR					
	KR					
	LR					
	MR					
	NR					

FOREIGN PATENT DOCUMENTS

	Document Number	Date MM/YY YY	Country	Inventor Name	English Abstract		Translation Readily Available	
					Enclosed	No	Enclose	No
<i>u</i>	OR JP 2001-167475 A	06/2001	Japan	NONAKA et al.	x			
<i>u</i>	PR JP 2001-126308 A	05/2001	Japan	ARAI et al.	x			
<i>u</i>	QR JP 11-339314 A	12/1999	Japan	NAGINO et al.	x			
<i>u</i>	RR JP 03-125343 A	05/1991	Japan	SUZUKI et al.	x			
<i>u</i>	SR JP 10-116441 A	05/1998	Japan	ROSEN et al.	x			
<i>u</i>	TR JP 2000-339760 A	12/2000	Japan	KUSADA et al.	x			
<i>u</i>	UR JP 2001-014723 A	01/2001	Japan	HIROTSUNE et al.	x			
<i>u</i>	VR JP 2002-298433 A	10/2002	Japan	YUZUSU et al.	x			
	WR				x			
	XR							

OTHER (Including in this order: Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

<i>u</i>	YR	Japanese Office Action dated March 29, 2005 for Appln. No. 2002-339437			
<i>u</i>	ZR	Japanese Office Action dated March 29, 2005 for Appln. No. 2002-342896			
	AAR				
	BBR				

Examiner *[Signature]* Date Considered: 4/21/06

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

FORM PTO-1449 (modified)
To: U.S. Department of Commerce
(PW FORM PAT-1449)
Patent and Trademark Office

Atty.
Dkt. No.

M#

Client Ref.

0306969

T7KO-03S1080

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

Applicant: SUMIO ASHIDA et al.

Appln. No.: UNASSIGNED

Filing Date: November 21, 2003

Examiner: UNKNOWN

Group Art Unit: UNKNOWN

Date: November 21, 2003

Page

1

of

1

U.S. PATENT DOCUMENTS

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
	AR					
	BR					
	CR					
	DR					
	ER					
	FR					
	GR					
	HR					
	IR					

	Document Number	Date MM/YYYY	Country	Inventor Name	Enclosed	No	Enclose	No
<i>u</i>	JR 2003-67974	03/2003	Japan	Inao et al.	X			X
<i>u</i>	KR 2000-322770	11/2000	Japan	Osada et al.	X			X
<i>u</i>	LR 2001-232941	08/2001	Japan	Ashida et al.	X			X
<i>u</i>	MR 11-213446	08/1999	Japan	Ota et al.	X			X
<i>u</i>	NR 2000-222777	08/2000	Japan	Uno et al.	X			X
<i>u</i>	OR 2002-279693	09/2002	Japan	Miyamoto et al.	X			X
	PR 2003-233931	08/2003	Japan			X		X
	QR							
	RR							
	SR							

OTHER (Including in this order: Author, Title, Periodical Name, Date, Pertinent Pages, etc.)								
<i>u</i>	TR	T. Inase et al., "Investigation of Protective Layer for High Transfer Rate Phase Change Optical Disk," Tokyo Research Lab., Tosoh Corp., pages 37-42 (12/2001)						
<i>u</i>	UR	Mayumi Uno et al., "Acceleration of crystallization process by nitride interface layer," Optical Disk Systems Development Center, Matsushita Electric Industrial Co., Ltd., pages 85-90 (11/1999)						
<i>u</i>	VR	Rie Kojima et al., "Ge-Sn-Sb-Te Phase-change Recording Material Having High Crystallization Speed," Optical Disk Systems Development Center, Matsushita Electric Industrial Co., Ltd., pages 36-41 (11-12/2000)						
<i>u</i>	WR	Michiaki Shinotsuka et al., "High-speed Blue-laser Recording on the Double-decker Phase Change Disk with High-Reliability," Research and Development Group, Ricoh Company, Ltd., IEEE 2002, pages 234-236 (2002)						
	XR							
	YR							

Examiner

Date Considered:

11/21/06

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.